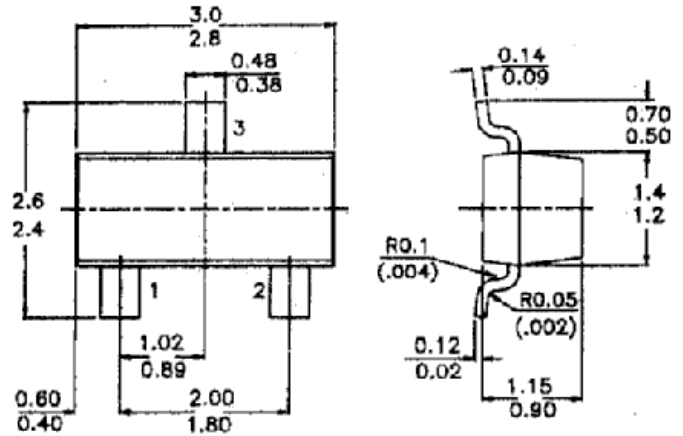
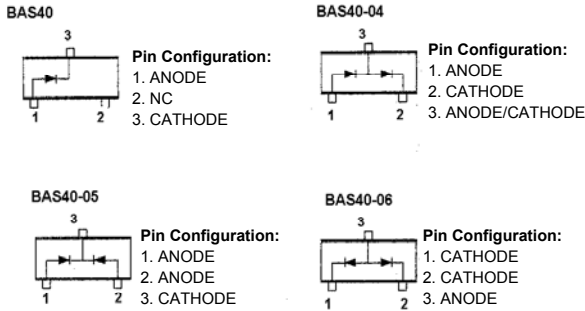


SILICON PLANAR SCHOTTKY DIODE



SOT-23 SMD Package

Absolute Maximum Ratings (per diode)

General Purpose Schottky Diode for High Speed switching

DESCRIPTION	SYMBOL	VALUE	UNITS
Reverse Voltage	V_R	40	V
Forward Current	I_F	120	mA
Surge Forward Current $t=10\text{ms}$	I_{FSM}	200	mA
Power Dissipation $T_a = 25^\circ\text{C}$	P_D	250	mW
Storage Temperature Range	T_{stg}	- 55 to +150	°C
Junction Temperature	T_j	150	

Thermal Resistance

From junction to ambient	$R_{th(j-a)}$ *	430	K/W
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*Mounted on a ceramic substrate of 10mm x 8mm x 0.6mm

Electrical Characteristics ($T_a=25^\circ\text{C}$ unless otherwise specified) (per diode)

DESCRIPTION	SYMBOL	TEST CONDITION	MIN	MAX	UNITS
Reverse Braekdown Voltage	V_R	$I_R = 10\mu\text{A}$	40		V
Reverse Current	I_R	$V_R = 30\text{V}$ $V_R = 40\text{V}$		1 10	μA
Forward Voltage	V_F	$I_F = 1\text{mA}$ $I_F = 10\text{mA}$ $I_F = 40\text{mA}$		0.38 0.50 1.00	V
Diode Capacitance	C_T	$V_R = 40\text{V}$		5.00	pF